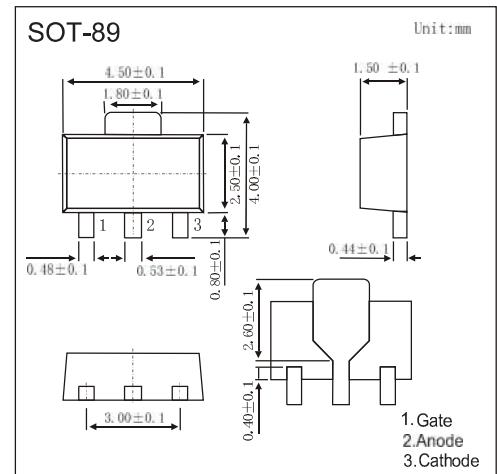
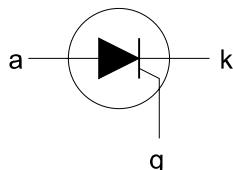


Silicon Controlled Rectifiers

■ Features

- Blocking voltage to 600 V
- Average on-state current to 0.5 A
- General purpose switching



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Repetitive peak off-state voltages	V _{DRM} ,V _{RRM}	600	V
Average on-state current	I _{T(AV)}	0.5	A
RMS on-state current	I _{T(RMS)}	0.8	A
Non-repetitive peak on-state current	I _{TSM}	8	A

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Repetitive peak off-state voltages	V _{DRM}		600			V
Average on-state current	I _{T(AV)}	Half sine wave; T _{lead} ≤ 83 °C		0.5		A
RMS on-state current	I _{T(RMS)}	All conduction angles		0.8		A
Non-repetitive peak on-state current	I _{TSM}	full sine wave; T _j = 25°C prior to surge	t = 10 ms t = 8.3 ms	8 9		A
I ² t for fusing	I ² t	t = 10 ms		0.32		A ² s
Repetitive rate of rise of on-state current after triggering	dI _T /dt	I _{TM} = 2 A; I _G = 10m A; dI _G /dt = 100m A/μs		50		A/μs
Peak gate current	I _{GM}			1		A
Peak gate voltage	V _{GM}			5		V
Peak gate power	P _{GM}			2		W
Average gate power	P _{G(AV)}	over any 20 ms period		0.1		W
Thermal resistance junction to ambient	R _{θJA}	PCB mounted, lead length=4mm	150			K/W
Storage temperature	T _{stg}		-40	150		°C
Operating junction temperature	T _j			125		°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Gate trigger current	I _{GT}	V _D = 12 V; I _T = 10m A, gate open circuit		50	200	μ A
Latching current	I _L	V _D = 12 V; I _{GT} = 0.5mA R _{GK} =1K Ω		2	6	mA
Holding current	I _H	V _D = 12 V; I _{GT} = 0.5mA R _{GK} =1K Ω		2	5	
On-state voltage	V _T	I _T = 1 A		1.2	1.35	V
Gate trigger voltage	V _{GT}	V _D = 12 V; I _T = 10mA, gate open circuit		0.5	0.8	V
		V _D = V _{DRM(max)} ; I _T = 10mA; T _j = 125 °C	0.2	0.3		V
Off-state leakage current	I _{D,IR}	V _D = V _{DRM(max)} ; V _R =V _{RMM(max)} T _j = 125 °C R _{GK} =1K Ω		0.05	0.1	mA
Critical rate of rise of off-state voltage	dV _D /dt	V _{DM} = 67% V _{DRM(max)} ; T _j = 125 °C; exponential R _{GK} =1K Ω		25		V/ μ s
Gate controlled turn-on time	t _{gt}	I _{TM} =2A;V _D =V _{DRM(max)} ; I _G =10mA dI _G /dt = 0.1 A/ μ s		2		μ s
Circuit commutated turn-off time	t _q	I _{TM} = 1.6 A; V _D = 67%V _{DRM(max)} ; T _j =125°C;VR=35V;R _{GK} =1kΩ dI _{TM} /dt = 30 A/ μ s;V _D /dt = 2V/ μ s		100		μ s

■ Typical Characteristics

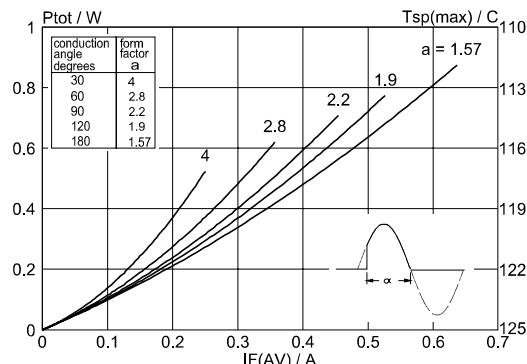


Fig.1. Maximum on-state dissipation, P_{tot} , versus average on-state current, $I_{T(AV)}$, where a = form factor = $I_{T(RMS)} / I_{T(AV)}$

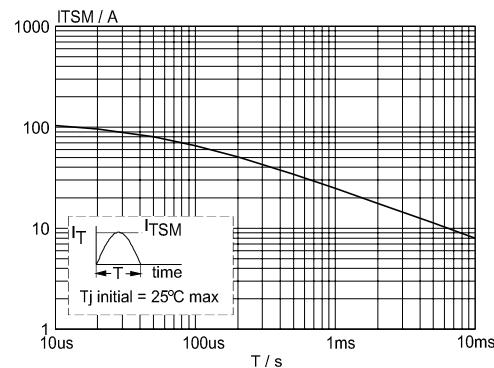


Fig.2. Maximum permissible non-repetitive peak on-state current I_{TSM} , versus pulse width t_p , for sinusoidal currents, $t_p \leq 10\text{ms}$.

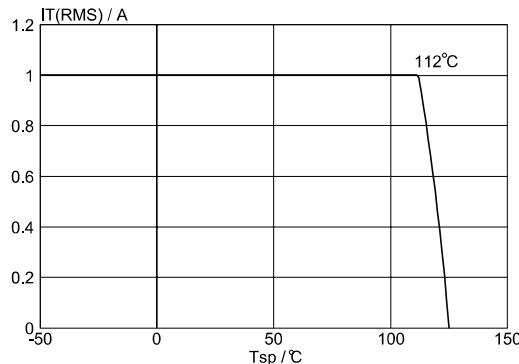


Fig.3. Maximum permissible rms current $I_{T(RMS)}$, versus solder point temperature T_{sp} .

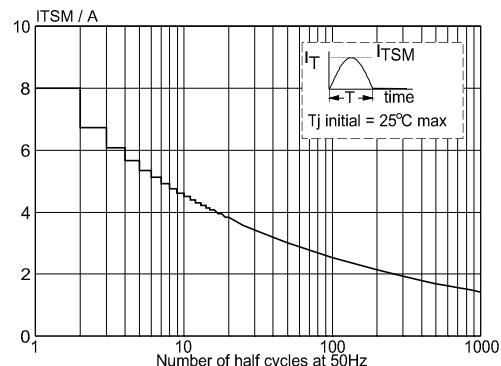


Fig.4. Maximum permissible non-repetitive peak on-state current I_{TSM} , versus number of cycles, for sinusoidal currents, $f = 50\text{ Hz}$.

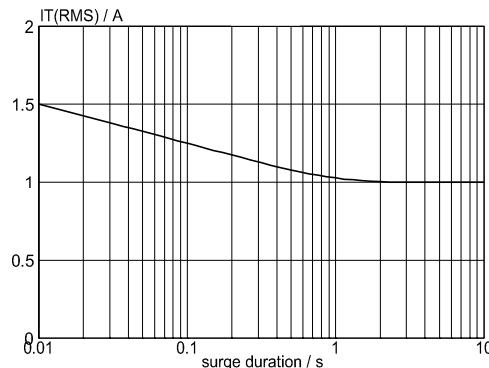


Fig.5. Maximum permissible repetitive rms on-state current $I_{T(RMS)}$, versus surge duration, for sinusoidal currents, $f = 50\text{ Hz}$; $T_{sp} \leq 112^\circ\text{C}$.

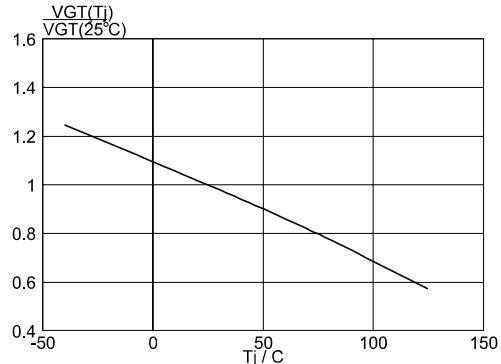


Fig.6. Normalised gate trigger voltage $V_{GT}(T_j) / V_{GT}(25^\circ\text{C})$, versus junction temperature T_j .

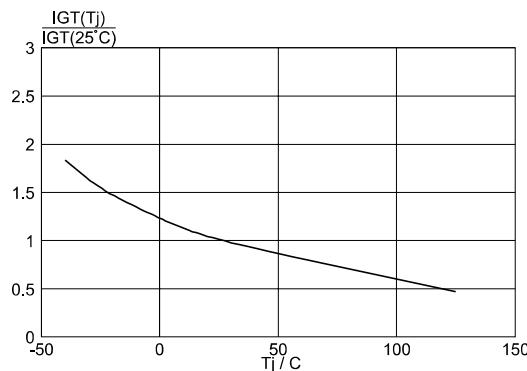


Fig.7. Normalised gate trigger current $I_{GT}(T_j)/I_{GT}(25^\circ C)$, versus junction temperature T_j .

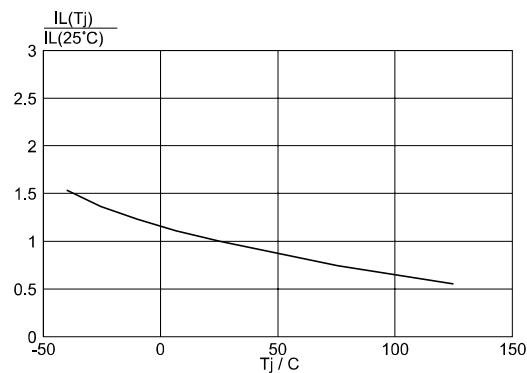


Fig.8. Normalised latching current $I_L(T_j)/I_L(25^\circ C)$, versus junction temperature T_j , $R_{GK} = 1 \text{ k}\Omega$.

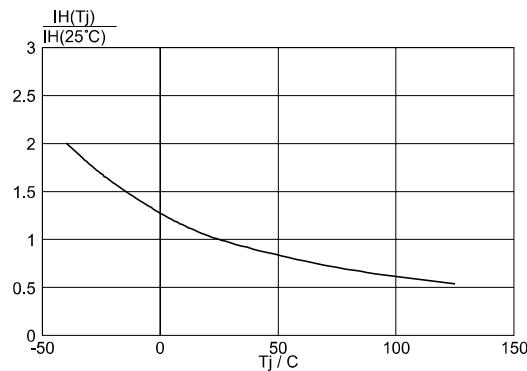


Fig.9. Normalised holding current $I_H(T_j)/I_H(25^\circ C)$, versus junction temperature T_j , $R_{GK} = 1 \text{ k}\Omega$.

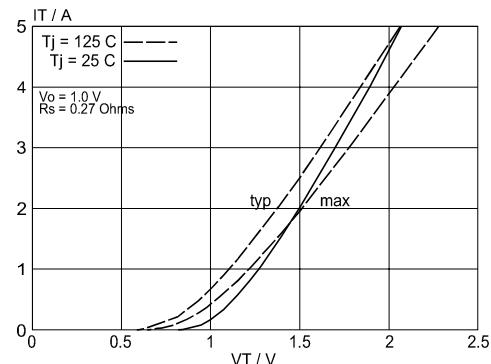


Fig.10. Typical and maximum on-state characteristic.

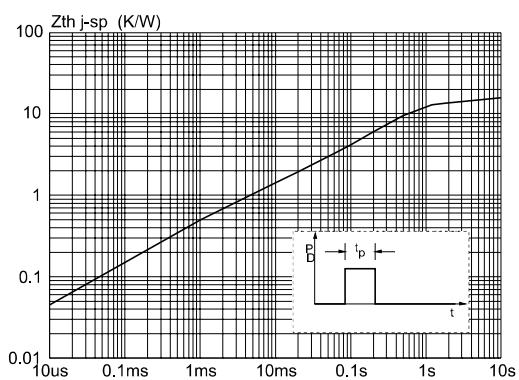


Fig.11. Transient thermal impedance $Z_{th(j-sp)}$, versus pulse width t_p .

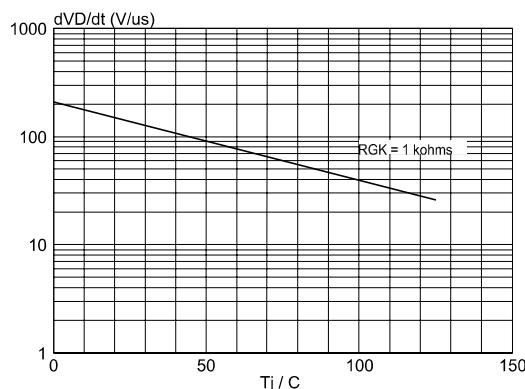
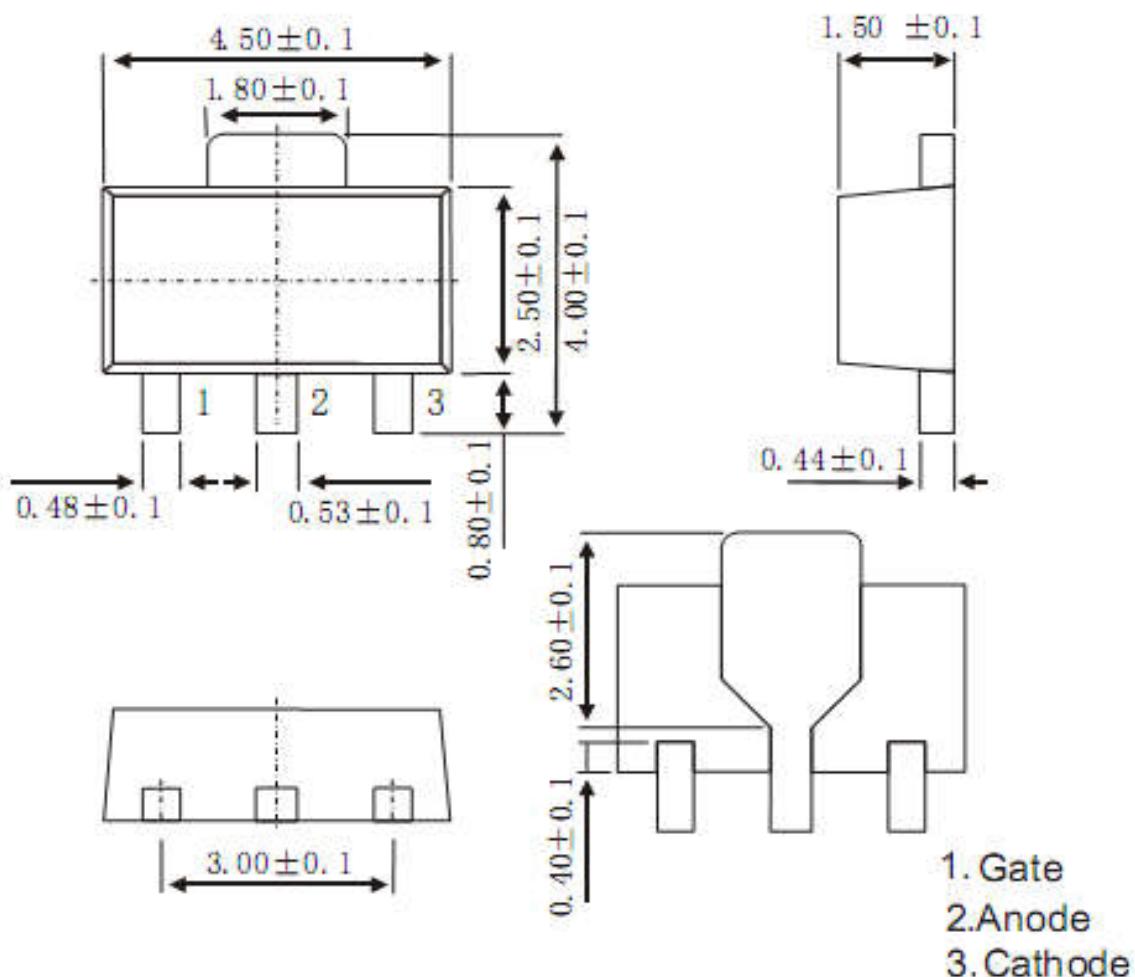


Fig.12. Typical, critical rate of rise of off-state voltage, dV_D/dt versus junction temperature T_j .

Package Outline

SOT-89

Unit:mm



Summary of Packing Options

Package	Package Description	Packing Quantity	Industry Standard
SOT-89	Tape/Reel,7"reel	1000	EIA-481-1

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